QIAOXIN N-Channel **Super Trench** Power MOSFET

Description

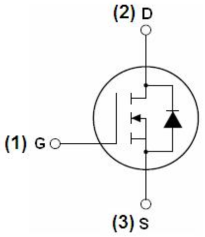
The VCRR 85T25VD uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g. This device is ideal for high-frequency switching and synchronous rectification.

General Features

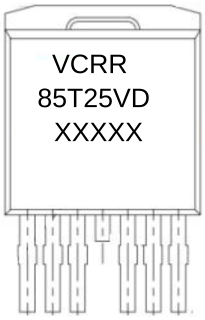
- V_{DS} =85V,I_D =250A
  $R_{DS(ON)}$ <2.0mΩ @ V_{GS}=10V
- Excellent gate charge x $R_{DS(on)}$ product
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

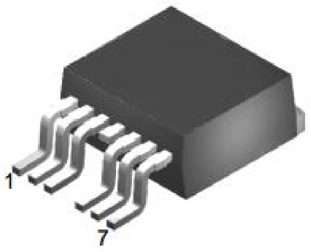
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



Schematic diagram



Marking and pin assignment



TO-263-7L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package
VCRR 85T25VD		TO-263-7L

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	85	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	250	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	180	A
Pulsed Drain Current	I_{DM}	1000	A
Maximum Power Dissipation	P_D	300	W
Derating factor		2	W/℃
Single pulse avalanche energy (Note 1)	E_{AS}	2000	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	0.5	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

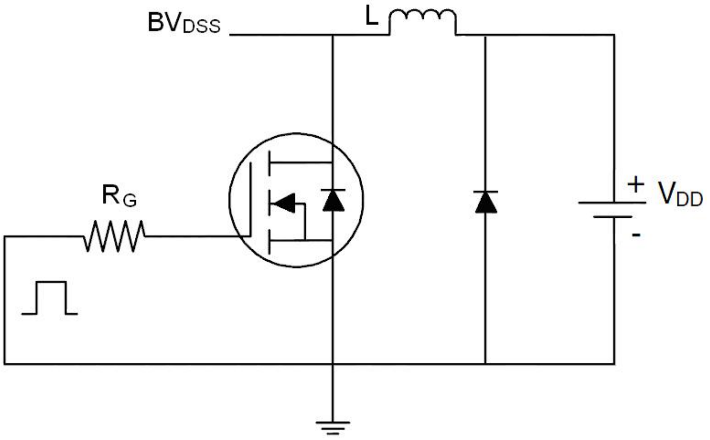
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	85		-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=85V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	2.5	3.5	4.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=100A	-	1.7	2.0	mΩ
Forward Transconductance	g_{FS}	V_{DS}=10V,I_D=100A	-	90	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	V_{DS}=40V,V_{GS}=0V, F=1.0MHz	-	10700	-	PF
Output Capacitance	C_{oss}		-	1700	-	PF
Reverse Transfer Capacitance	C_{rss}		-	76	-	PF
Switching Characteristics (Note 2)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=40V,I_D=100A V_{GS}=10V,R_G=1.6Ω	-	28	-	nS
Turn-on Rise Time	t_r		-	73	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	86	-	nS
Turn-Off Fall Time	t_f		-	33	-	nS
Total Gate Charge	Q_g	V_{DS}=40V,I_D=100A, V_{GS}=10V	-	142		nC
Gate-Source Charge	Q_{gs}		-	56		nC
Gate-Drain Charge	Q_{gd}		-	24		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	V_{GS}=0V,I_F= I_S	-		1.2	V
Diode Forward Current	I_S		-	-	250	A
Reverse Recovery Time	t_{rr}	T_J = 25°C, I_F = I_S di/dt = 100A/μs	-	115		nS
Reverse Recovery Charge	Qrr		-	320		nC

Notes:

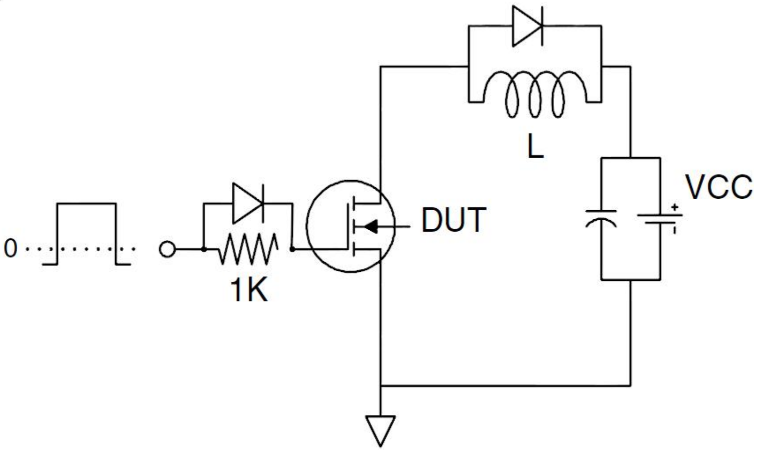
1. EAS condition : Tj=25℃,V_{DD}=40V,V_G=10V,L=0.5mH,Rg=25Ω
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsin k, assuming a maximum junction temperature of TJ(MAX)=175° C. The SOA curve provides a single pulse rating.

Test Circuit

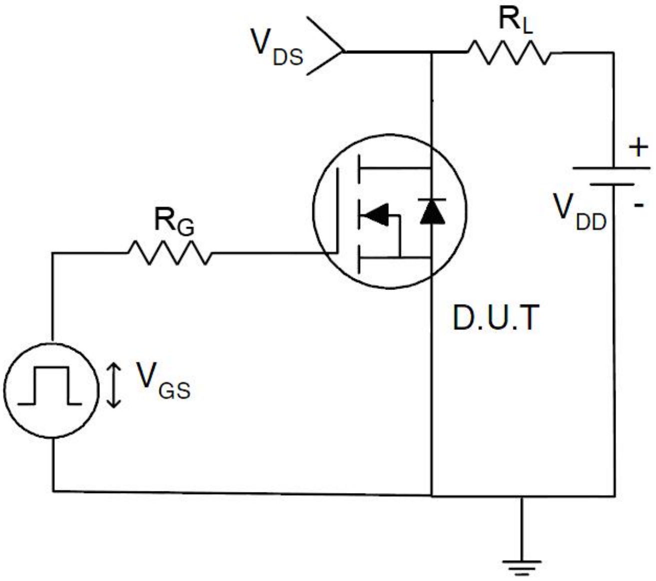
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics

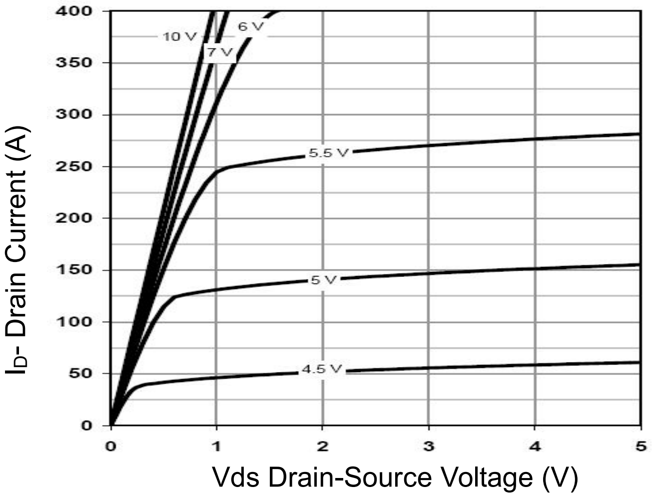


Figure 1 Output Characteristics

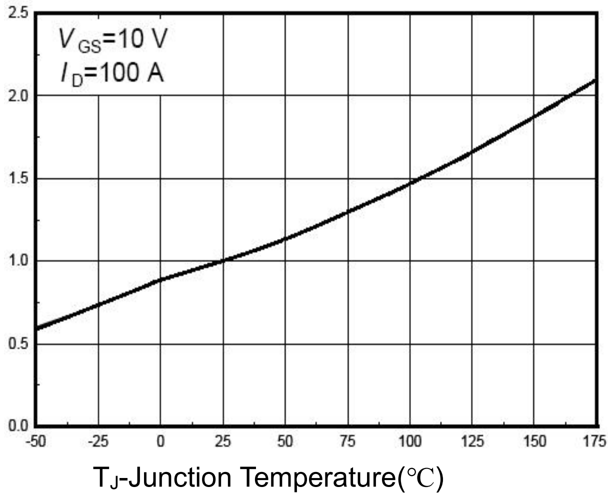


Figure 4 Rdson-JunctionTemperature

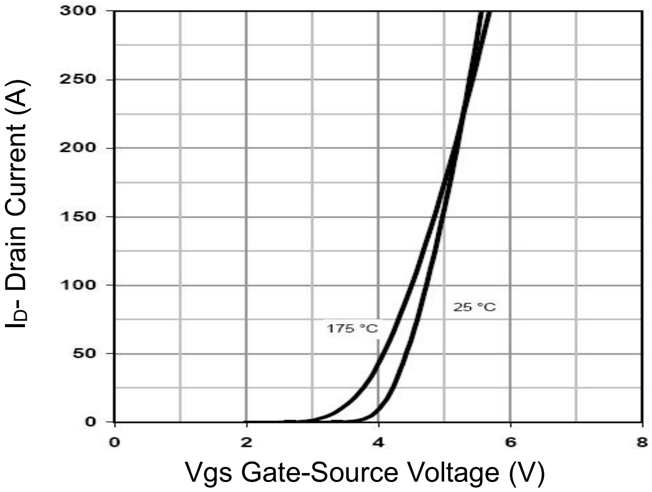


Figure 2 Transfer Characteristics

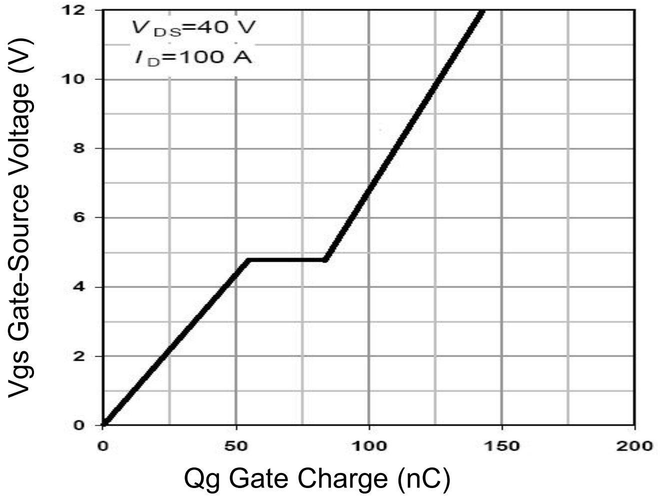


Figure 5 Gate Charge

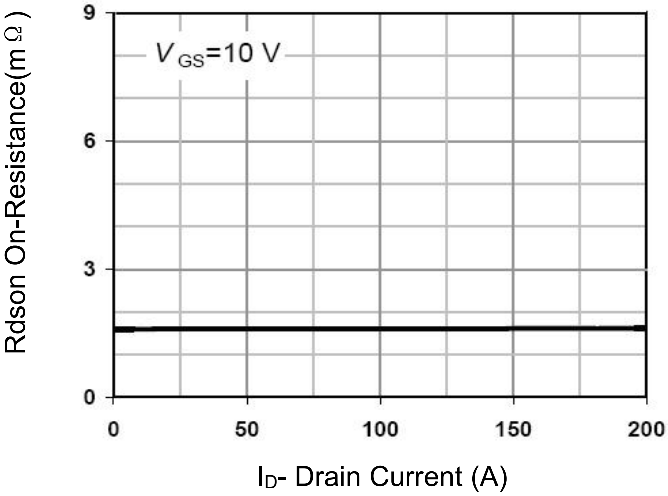


Figure 3 Rdson- Drain Current

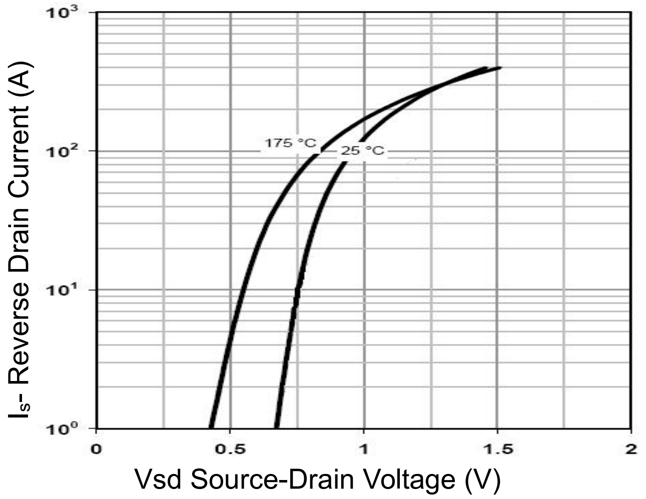


Figure 6 Source- Drain Diode Forward

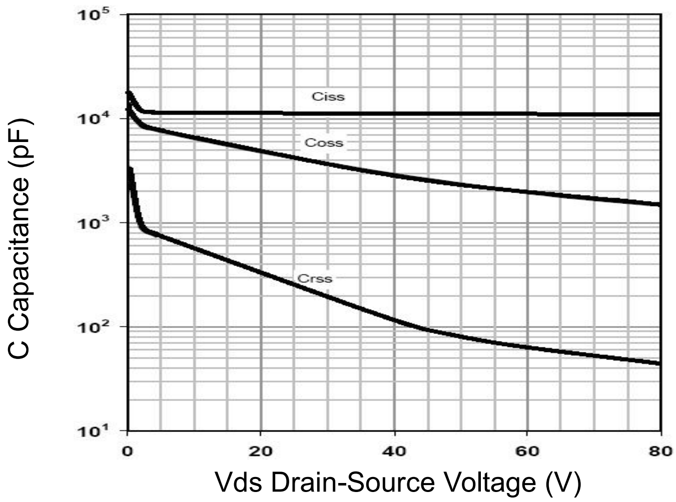


Figure 7 Capacitance vs Vds

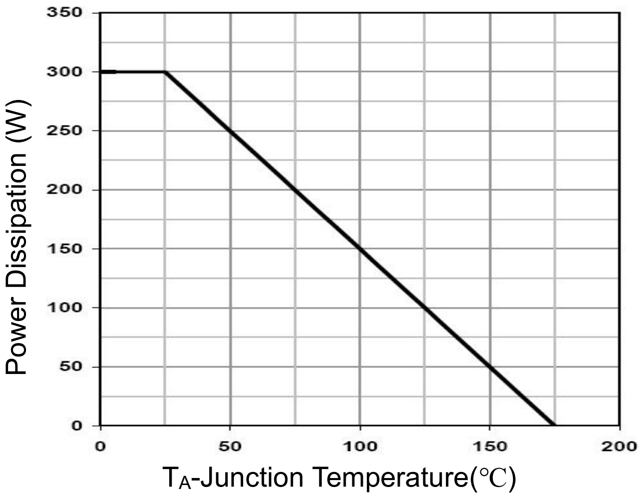


Figure 9 Power De-rating

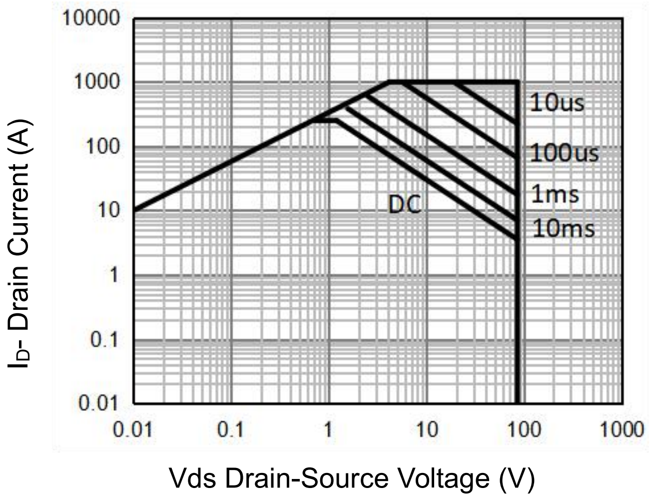


Figure 8 Safe Operation Area (Note 3)

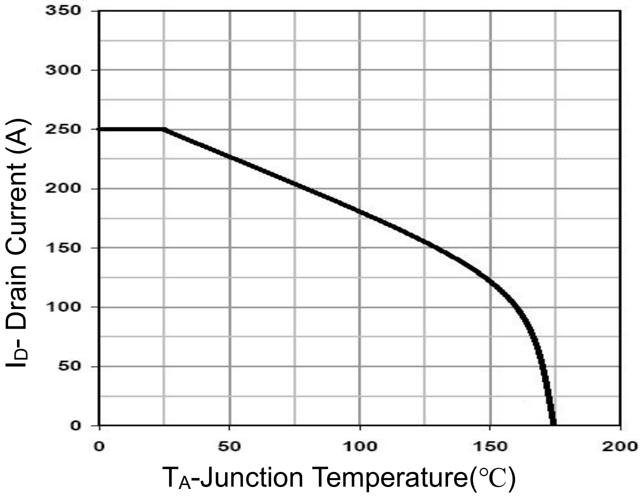


Figure 10 Current De-rating

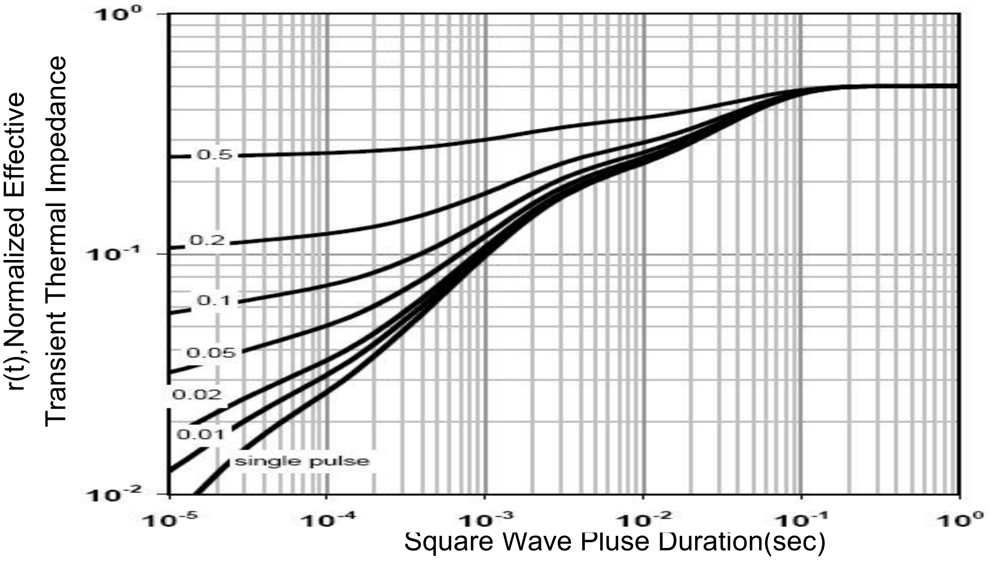
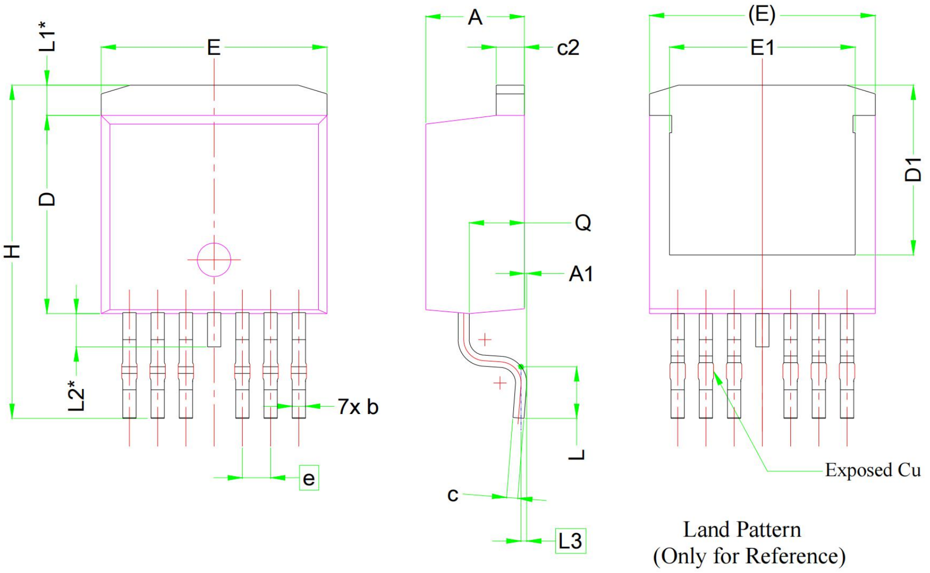
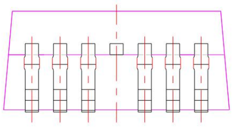


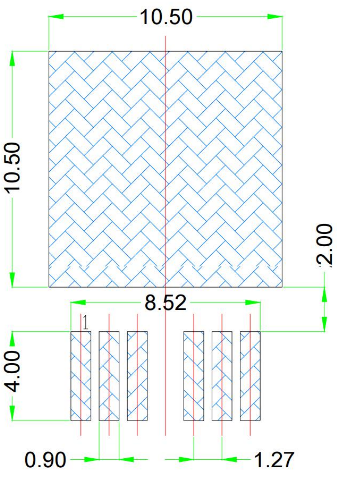
Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263-7L Package Information





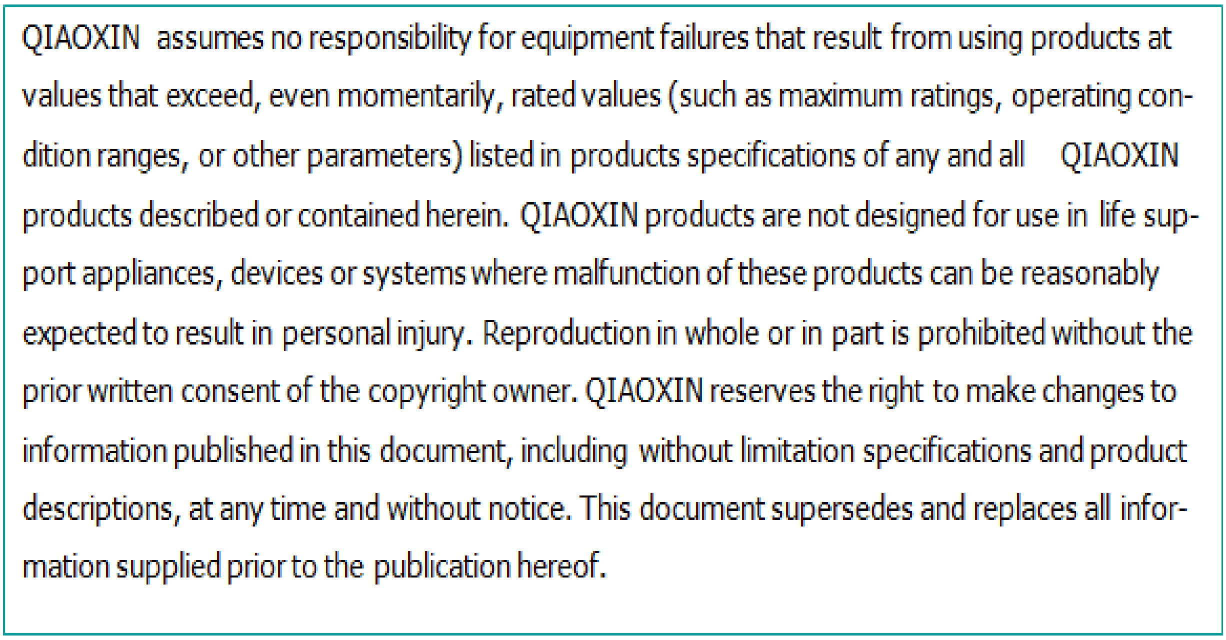
Land Pattern
(Only for Reference)



Note:
1. All Dimensions Are In mm.
2. Dimension D & E Do Not Include Mold Flash.
   Mold Flash Shall Not Exceed 0.127mm Pre Side.
   These Dimensions Are Measured At The Outermost
   Extreme Of The Plastic Body.
3. Thermal Pad Contour Optional Within Dimensions E, L1, D1 & E1.
4. Dimension D1 & E1 Establish A Minmum Mounting Surface for
   The Thermal Pad.
5. "*" is reference .

SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.50	0.60	0.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86	7.65	---
E	9.96	10.16	10.36
E1	8.20	8.35	8.50
e	1.27 BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36 REF.		
L2	1.50 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70

Attention



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